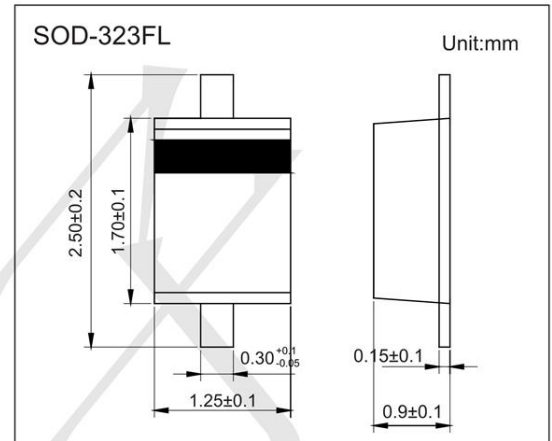


## Features

- Low forward voltage
- Reverse voltage  $V_R \leq 100$  V
- Low capacitance
- High-speed switching
- Very small and flat lead SMD plastic package



### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Reverse Voltage	$V_{RM}$	100	V
Forward Current	$I_F$	250	mA
Non-Repetitive Peak Forward Current	$I_{FSM}$	2.5	A
Power Dissipation (Note.1)	$P_d$	400	mW
(Note.2)		715	
Thermal Resistance Junction to Ambient (Note.1)	$R_{\theta JA}$	310	$^\circ\text{C}/\text{W}$
(Note.2)		175	
Thermal Resistance Junction to Solder Point	$R_{\theta JSP}$	35	
Junction Temperature	$T_J$	150	$^\circ\text{C}$
Storage Temperature range	$T_{stg}$	-65 to 150	

Note.1: Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

Note.2: Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode  $1\text{ cm}^3$

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse breakdown voltage	V <sub>R</sub>	I <sub>R</sub> = 100 uA	100			V
Forward voltage	V <sub>F</sub>	I <sub>F</sub> = 0.1 mA			200	mV
		I <sub>F</sub> = 10 mA			350	
		I <sub>F</sub> = 10 mA , T <sub>J</sub> = -40°C			470	
		I <sub>F</sub> = 50 mA			475	
		I <sub>F</sub> = 50 mA , T <sub>J</sub> = -40°C			560	
		I <sub>F</sub> = 250 mA			850	
Reverse voltage leakage current	I <sub>R</sub>	V <sub>R</sub> = 1.5 V			0.5	uA
		V <sub>R</sub> = 1.5 V , T <sub>J</sub> = 60°C			12	
		V <sub>R</sub> = 10 V			0.8	
		V <sub>R</sub> = 10 V , T <sub>J</sub> = 60°C			20	
		V <sub>R</sub> = 50 V			2	
		V <sub>R</sub> = 50 V , T <sub>J</sub> = 60°C			44	
		V <sub>R</sub> = 75 V			4	
		V <sub>R</sub> = 75 V , T <sub>J</sub> = 60°C			80	
		V <sub>R</sub> = 100 V			9	
		V <sub>R</sub> = 100 V , T <sub>J</sub> = 60°C			120	
		V <sub>R</sub> = 100 V , T <sub>J</sub> = 85°C			600	
Junction capacitance	C <sub>j</sub>	V <sub>R</sub> = 0 V, f= 1 MHz			39	pF
		V <sub>R</sub> = 1 V, f= 1 MHz			21	
Reverse recovery time	t <sub>rr</sub>	I <sub>F</sub> =I <sub>R</sub> =10mA, I <sub>rr</sub> =0.1xI <sub>R</sub> , R <sub>L</sub> =100Ω			5.9	ns

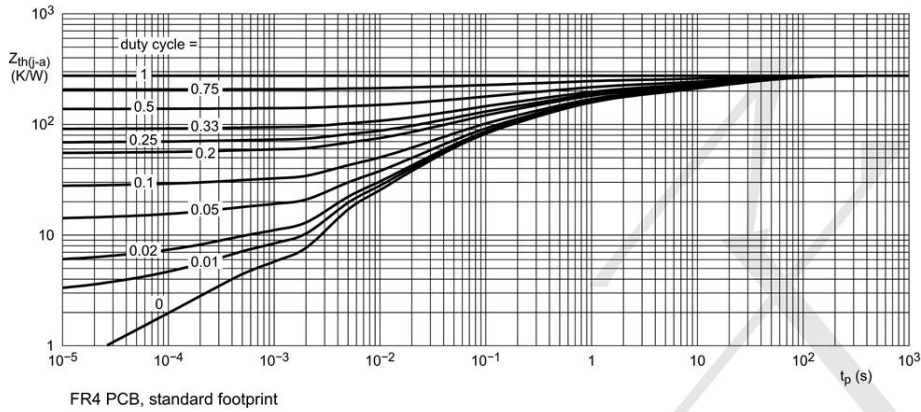


Fig 1. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

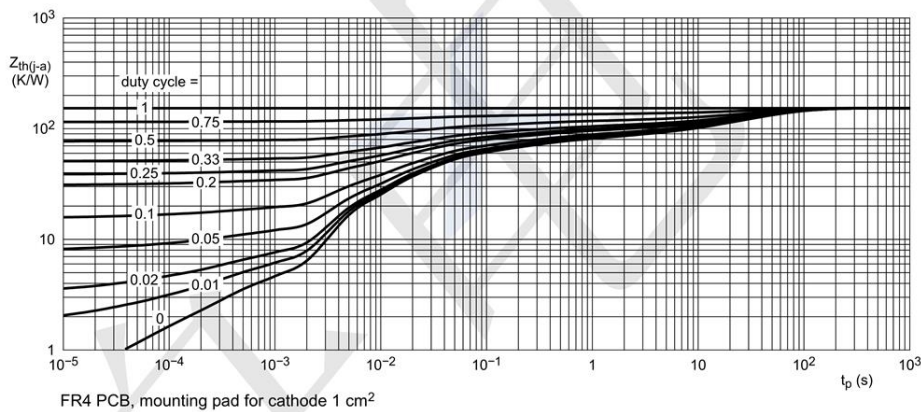
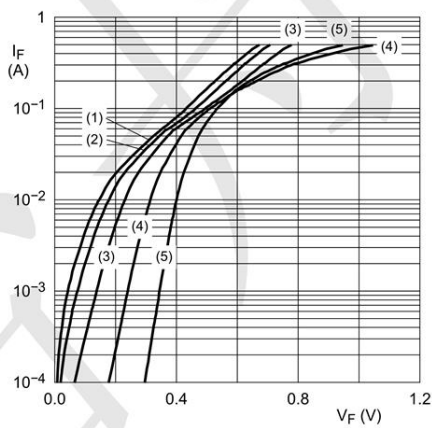
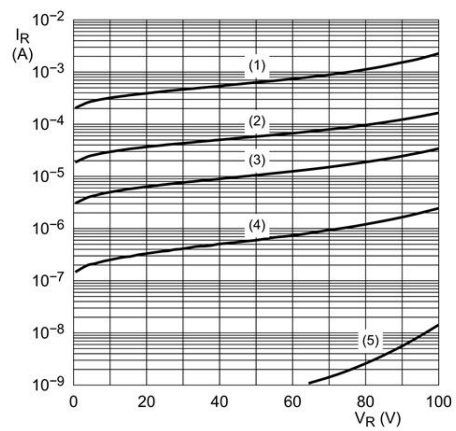


Fig 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



- (1)  $T_{amb} = 150\text{ }^{\circ}\text{C}$  (4)  $T_{amb} = 25\text{ }^{\circ}\text{C}$
- (2)  $T_{amb} = 125\text{ }^{\circ}\text{C}$  (5)  $T_{amb} = -40\text{ }^{\circ}\text{C}$
- (3)  $T_{amb} = 85\text{ }^{\circ}\text{C}$

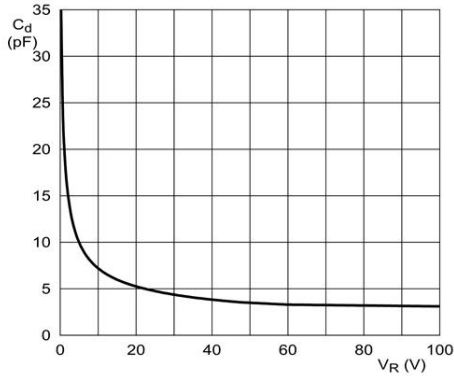
Fig 3. Forward current as a function of forward voltage; typical values



- (1)  $T_{amb} = 125\text{ }^{\circ}\text{C}$  (4)  $T_{amb} = 25\text{ }^{\circ}\text{C}$
- (2)  $T_{amb} = 85\text{ }^{\circ}\text{C}$  (5)  $T_{amb} = -40\text{ }^{\circ}\text{C}$
- (3)  $T_{amb} = 60\text{ }^{\circ}\text{C}$

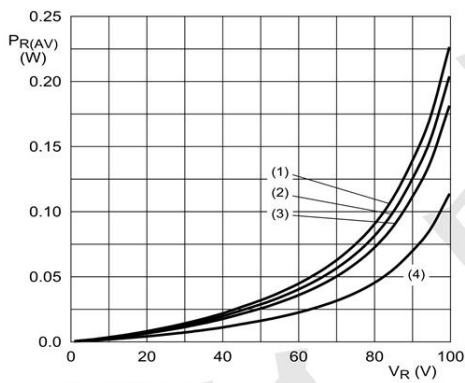
Fig 4. Reverse current as a function of reverse voltage; typical values

■ Typical Characteristics



f = 1 MHz; T<sub>amb</sub> = 25 °C

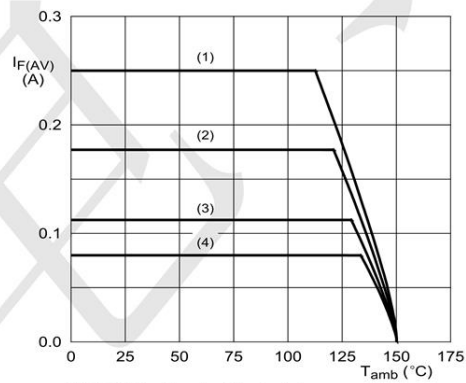
**Fig 5. Diode capacitance as a function of reverse voltage; typical values**



T<sub>j</sub> = 125 °C

(1) δ = 1 (3) δ = 0.8  
(2) δ = 0.9 (4) δ = 0.5

**Fig 6. Average reverse power dissipation as a function of reverse voltage; typical values**

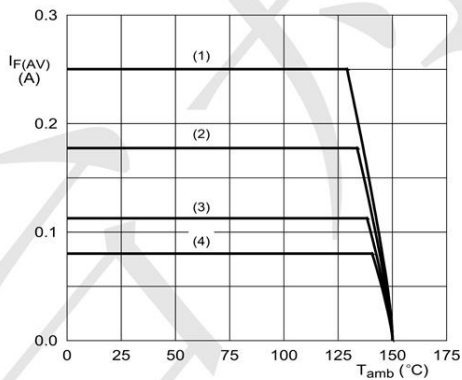


FR4 PCB, standard footprint

T<sub>j</sub> = 150 °C

(1) δ = 1; DC (3) δ = 0.2; f = 20 kHz  
(2) δ = 0.5; f = 20 kHz (4) δ = 0.1; f = 20 kHz

**Fig 7. Average forward current as a function of ambient temperature; typical values**

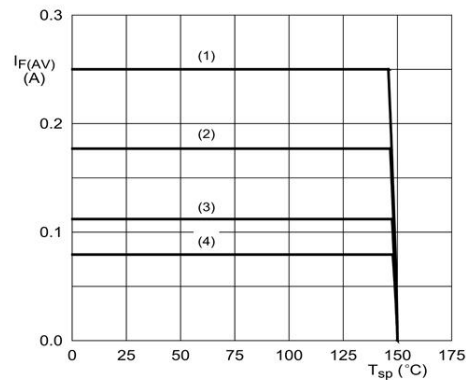


FR4 PCB, mounting pad for cathode 1 cm<sup>2</sup>

T<sub>j</sub> = 150 °C

(1) δ = 1; DC (3) δ = 0.2; f = 20 kHz  
(2) δ = 0.5; f = 20 kHz (4) δ = 0.1; f = 20 kHz

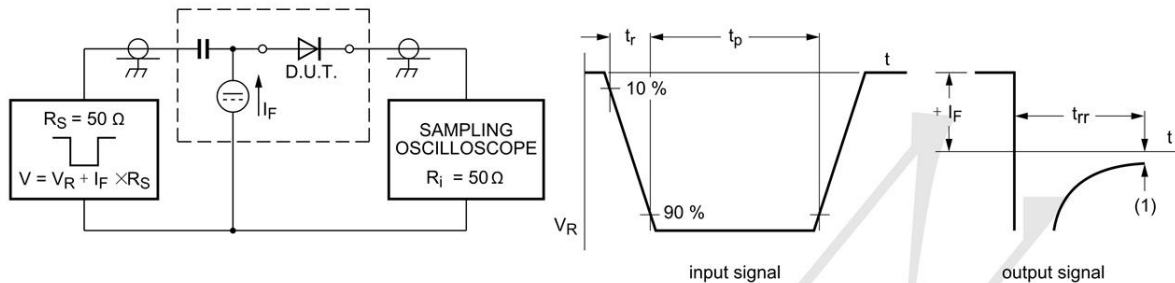
**Fig 8. Average forward current as a function of ambient temperature; typical values**



T<sub>j</sub> = 150 °C

(1) δ = 1; DC (3) δ = 0.2; f = 20 kHz  
(2) δ = 0.5; f = 20 kHz (4) δ = 0.1; f = 20 kHz

**Fig 9. Average forward current as a function of solder point temperature; typical values**

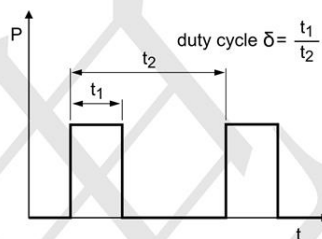


(1)  $I_R = 1 \text{ mA}$

Input signal: reverse pulse rise time  $t_r = 0.6 \text{ ns}$ ; reverse voltage pulse duration  $t_p = 100 \text{ ns}$ ; duty cycle  $\delta = 0.05$

Oscilloscope: rise time  $t_r = 0.35 \text{ ns}$

**Fig 10. Reverse recovery time test circuit and waveforms**

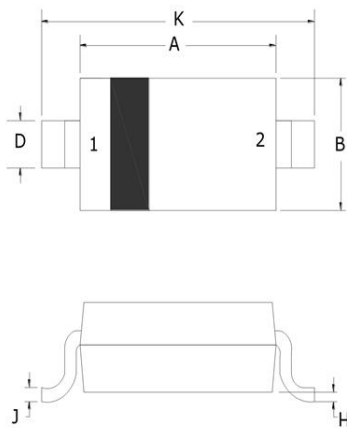


**Fig 11. Duty cycle definition**

The current ratings for the typical waveforms as shown in Figure 7, 8 and 9 are calculated according to the equations:  $I_{FAV} = I_M \times \delta$  with  $I_M$  defined as peak current,

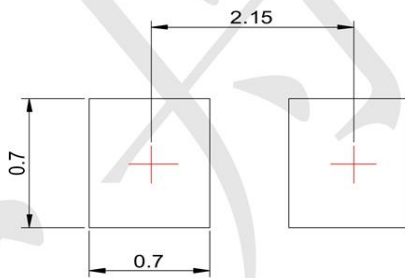
$I_{RMS} = I_{F(AV)}$  at DC, and  $I_{RMS} = I_M \times \sqrt{\delta}$  with  $I_{RMS}$  defined as RMS current.

### Outline Drawing - SOD-323



Dim	Millimeters		Inches	
	Min	Max	Min	Max
A	1.60	1.80	0.063	0.071
B	1.2	1.40	0.047	0.055
C	0.80	0.90	0.031	0.035
D	0.25	0.35	0.010	0.014
E	0.15REF		0.006REF	
H	0	0.10	0	0.004
J	0.08	0.15	0.003	0.006
K	2.50	2.70	0.098	0.106

### Land Pattern - SOD-323



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